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**(54) TRANSPARENT  
ELECTROCONDUCTIVE  
FILM-ATTACHED GLASS  
HAVING HIGH RESISTANCE**

(57) Abstract:

PURPOSE: To obtain transparent electroconductive film-attached glass having high resistance and excellent in uniformity by forming a film of silicon dioxide onto a glass substrate and forming a transparent electroconductive film thereon to provide a film having two layer

structure.

CONSTITUTION: Silicon dioxide film containing phosphorus in an amount of 0.01-10wt.% and/or boron in an amount of 0.01-10wt.% based on silicon dioxide is formed on a transparent glass substrate in a film thickness of 60-150nm. A transparent electroconductive film having 1.7-2.2 refractive index, 200-3000 $\Omega$ /square and  $\pm$  2% linearity value is formed in a film thickness of 10-30nm thereon to provide the objective transparent electroconductive film attached glass. ITO, FTO, ATO, etc., is used as the transparent electroconductive film and silicon dioxide is formed into a film by a sputtering method, a CVD method, a spraying method, etc.

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